YEA SHIN TECHNOLOGY CO., LTD

YS2305

P- Channel Enhancement MOSFET

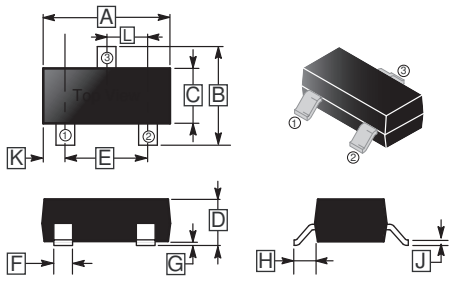
VDS= -20V, ID= -4.2A

DESCRIPTION

The YS2305 is the highest performance trench P-Ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the small power switching and load switch applications.

The YS2305 meet the RoHS and Green Product requirement with full function reliability approved.

SC-59



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	0.10 REF.	
B	2.10	3.00	H	0.40 REF.	
C	1.20	1.70	J	0.047	0.207
D	0.89	1.40	K	0.5 REF.	
E	2.00 Typ.		L	0.95 REF.	
F	0.30	0.50			

FEATURES

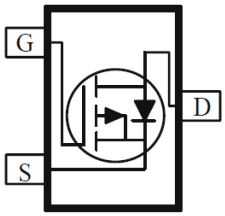
- Advanced High Cell Density Trench Technology
- Super Low Gate Charge

MARKING

2305

PACKAGE INFORMATION

Package	MPQ	Leader Size
SC-59	3K	7 inch



ORDER INFORMATION

Part Number	Type
YS2305	Lead (Pb)-free and Halogen-free

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Ratings		Unit
			≦10sec	Steady State	
Drain-Source Voltage		V_{DS}	-20		V
Gate-Source Voltage		V_{GS}	±12		V
Drain Current [1], @VGS= -10V	T_A=25℃	I_D	-4.2	-3.7	A
	T_A=70℃		-3.5	-3	
Pulsed Drain Current [3]		I_{DM}	-30		A
Power Dissipation	T_A=25℃	P_D	1.4		W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150		℃
Thermal Resistance Data					
Thermal Resistance Junction-Ambient [1]		$R_{\theta JA}$	≦10sec, 90		℃/W
			Steady State, 125		
Thermal Resistance Junction-Ambient [2]			270		
Thermal Resistance Junction-Case [1]		$R_{\theta JC}$	80		

ELECTRICAL CHARACTERISTICS (T_J=25℃ unless otherwise specified)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage		BV_{DSS}	-20	-	-	V	V_{GS}=0, I_D= -250μA
Gate Threshold Voltage		$V_{GS(th)}$	-0.5	-	-1.2	V	V_{DS}=V_{GS}, I_D= -250μA
Forward Transconductance		g_{fs}	-	5.6	-	S	V_{DS}= -5V,,I_D= -3A
Gate-Source Leakage Current		I_{GSS}	-	-	±100	nA	V_{GS}= ±12V
Drain-Source Leakage Current	T_J=25℃	I_{DSS}	-	-	-1	μA	V_{DS}= -20V, V_{GS}=0
	T_J=55℃		-	-	-5		V_{DS}= -20V, V_{GS}=0
Drain-Source On-Resistance [4]		$R_{DS(ON)}$	-	-	53	mΩ	V_{GS}= -10V, I_D= -4.5A
			-	-	65		V_{GS}= -4.5V, I_D= -4.2A
			-	-	100		V_{GS}= -2.5V, I_D= -2A
			-	-	250		V_{GS}= -1.8V, I_D= -1A
Total Gate Charge		Q_g	-	11.9	-	nC	I_D= -3A V_{DS}= -15V V_{GS}= -4.5V
Gate-Source Charge		Q_{gs}	-	1.8	-		
Gate-Drain (“Miller”) Charge		Q_{gd}	-	3	-		
Turn-on Delay Time		$T_{d(on)}$	-	6.6	-	nS	V_{DD}= -15V V_{GS}= -4.5V I_D= -3A R_G=3.3Ω R_L=5Ω
Rise Time		T_r	-	27.8	-		
Turn-off Delay Time		$T_{d(off)}$	-	46.2	-		
Fall Time		T_f	-	20.6	-		
Input Capacitance		C_{iss}	-	920	-	pF	V_{GS}=0 V_{DS}= -15V f=1MHz
Output Capacitance		C_{oss}	-	73	-		
Reverse Transfer Capacitance		C_{rss}	-	71	-		
Source-Drain Diode							
Forward on Voltage [4]		V_{SD}	-	-	-1.2	V	I_S= -1.2A, V_{GS}=0
Continuous Source Current [1]		I_S	-	-	-3.7	A	
Pulsed Source Current [3]		I_{SM}	-	-	-15		

Notes:
1. Surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2. When mounted on Min. copper pad.
3. Pulse width limited by maximum junction temperature.
4. The data tested by pulsed, pulse width≦300μs, duty cycle≦2%.

DEVICE CHARACTERISTICS

YS2305

CHARACTERISTIC CURVE

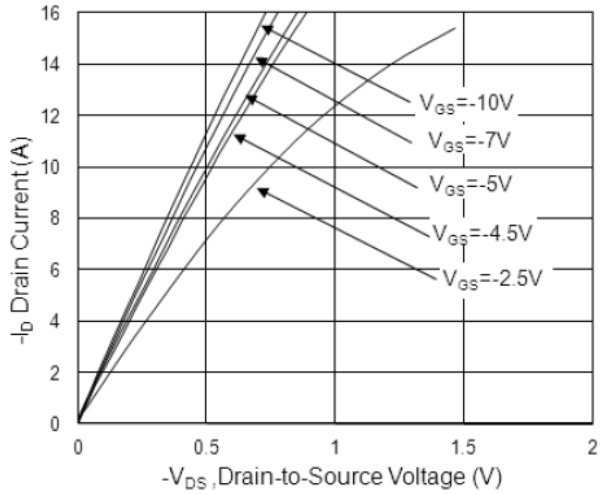


Fig.1 Typical Output Characteristics

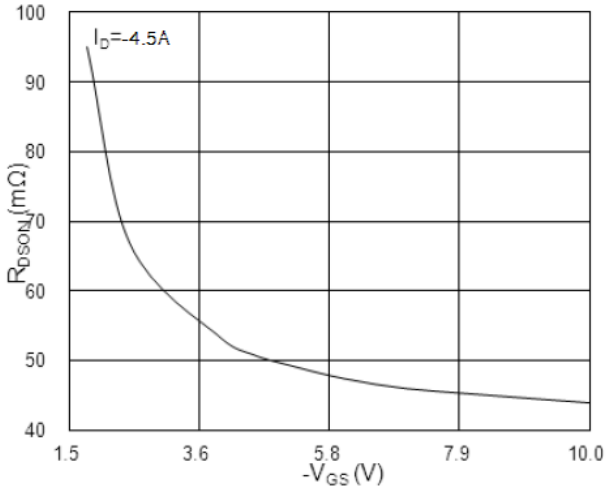


Fig.2 On-Resistance vs. G-S Voltage

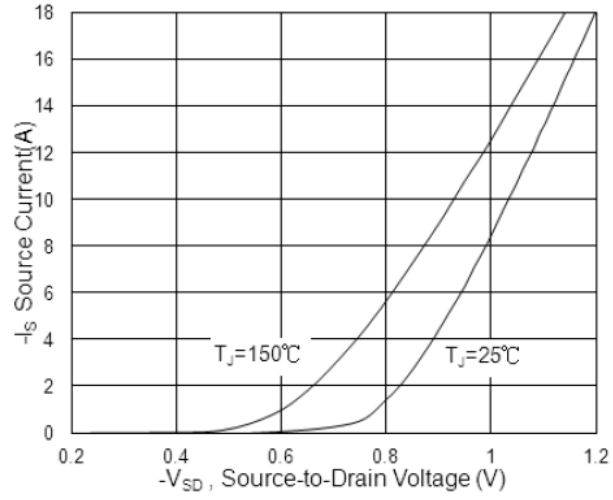


Fig.3 Forward Characteristics Of Reverse

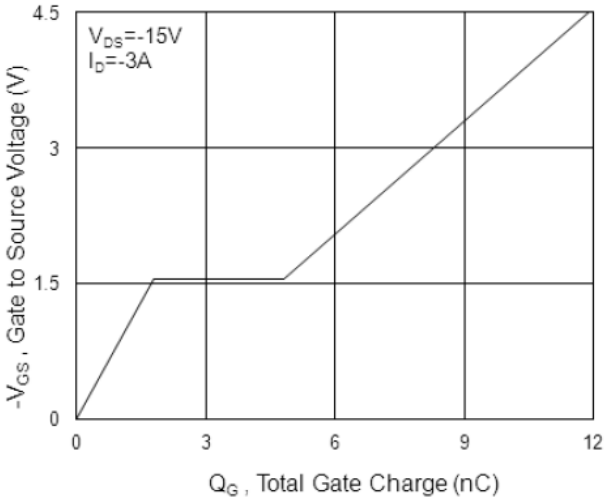


Fig.4 Gate-Charge Characteristics

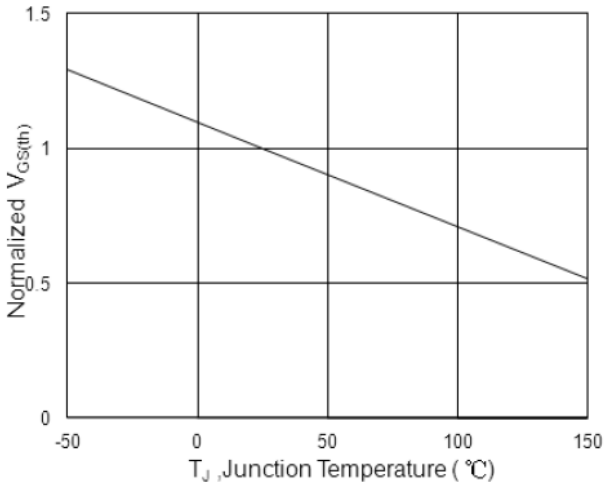


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

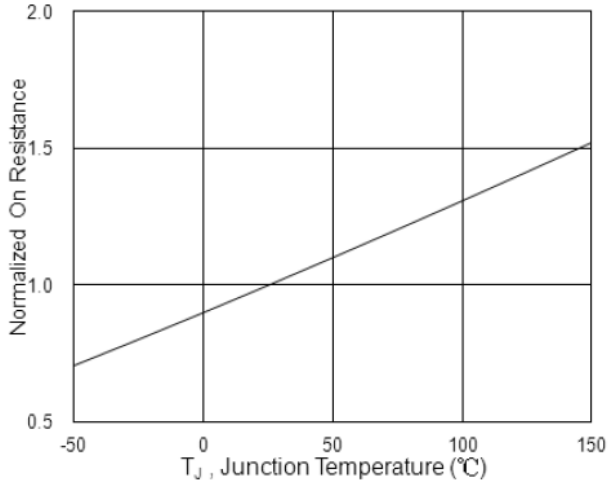


Fig.6 Normalized R_{DSON} vs. T_J

DEVICE CHARACTERISTICS

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CHARACTERISTIC CURVE

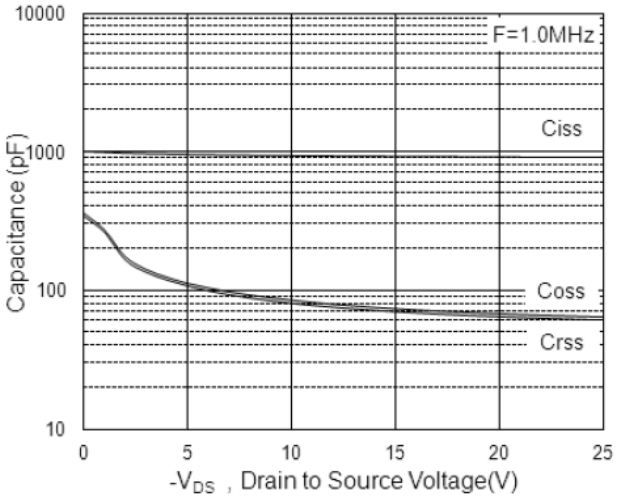

Fig.7 Capacitance

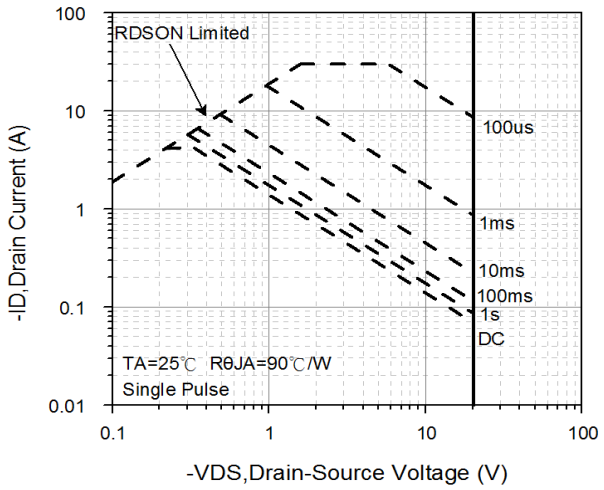

Fig.8 Safe Operating Area

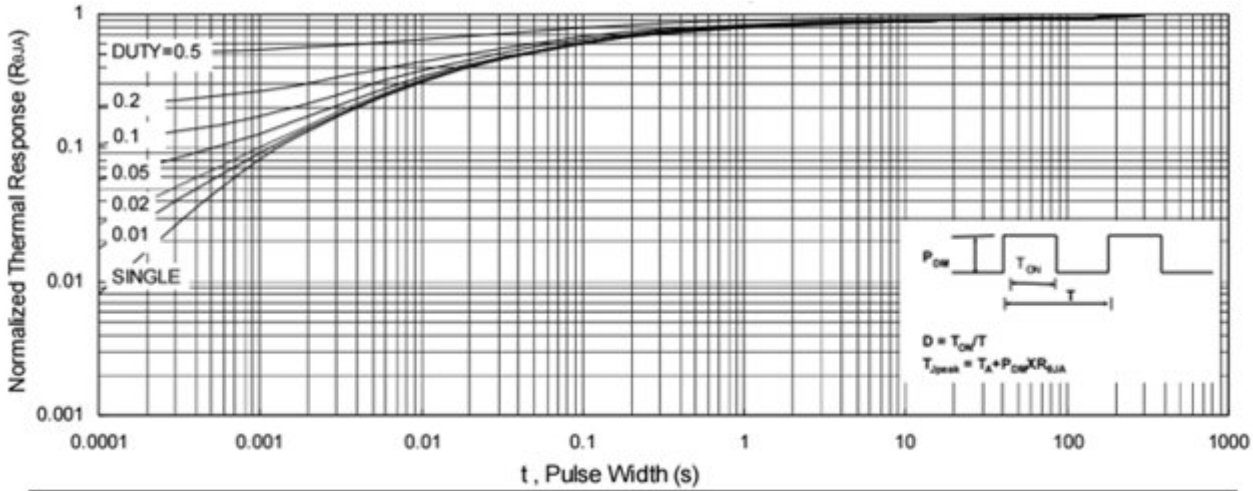

Fig.9 Normalized Maximum Transient Thermal Impedance

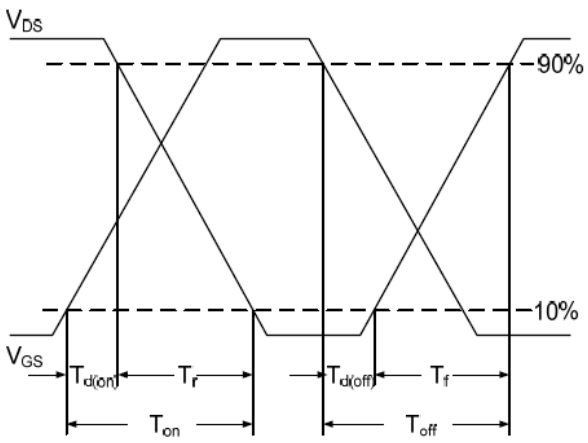

Fig.10 Switching Time Waveform

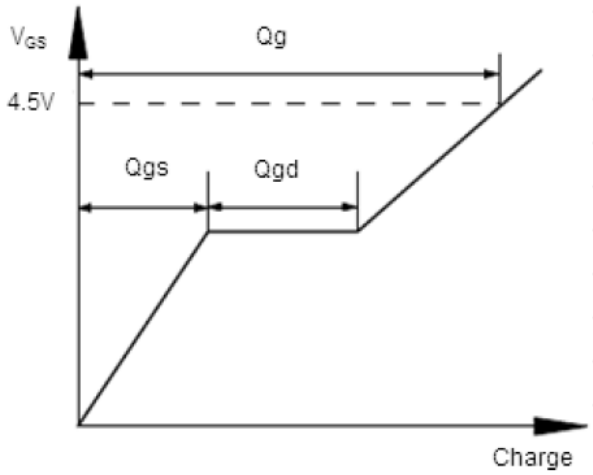

Fig.11 Gate Charge Waveform